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# FDS6575

# P-Channel 2.5V Specified PowerTrench MOSFET

# **General Description**

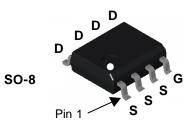
This PChannel 2.5V specified MOSFET is a rugged gate version of Fairchild Semiconductor's advanced PowerTrench process. It has been optimized for power management applications with a wide range of gate drive voltage (2.5V – 8V).

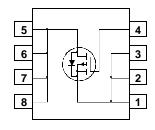
# **Applications**

- Power management
- Load switch
- · Battery protection

# **Features**

- -10 A, -20 V.  $R_{DS(ON)} = 13 \text{ m}\Omega$  @  $V_{GS} = -4.5 \text{ V}$  $R_{DS(ON)} = 17 \text{ m}\Omega$  @  $V_{GS} = -2.5 \text{ V}$
- · Low gate charge
- High performance trench technology for extremely low  $R_{\text{DS(ON)}}$
- High current and power handling capability





# Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		<b>–</b> 20	V
V <sub>GSS</sub>	Gate-Source Voltage		±8	V
I <sub>D</sub>	Drain Current - Continuous	(Note 1a)	-10	А
	- Pulsed		-50	
P <sub>D</sub>	Power Dissipation for Single Operation	(Note 1a)	2.5	W
		(Note 1b)	1.5	
		(Note 1c)	1.2	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range		-55 to +175	°C

# **Thermal Characteristics**

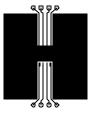
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1c)	125	°C/W
R <sub>eJC</sub>	Thermal Resistance, Junction-to-Case	(Note 1)	25	°C/W

**Package Marking and Ordering Information** 

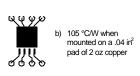
Device Marking	Device	Reel Size	Tape width	Quantity	
FDS6575	FDS6575	13"	12mm	2500 units	

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics			l		
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$ , Referenced to 25°C		-13		mV/°C
loss	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V},  V_{GS} = 0 \text{ V}$			-1	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage, Forward	$V_{GS} = 8 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage, Reverse	$V_{GS} = -8 \text{ V},  V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)			•		
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-0.4	-0.6	-1.5	V
$\Delta V_{GS(th)} \over \Delta T_J$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \mu A$ , Referenced to 25°C		3		mV/°C
R <sub>DS(on)</sub>	Static Drain–Source On–Resistance	$V_{GS} = -4.5 \text{ V},  I_D = -10 \text{ A}$ $V_{GS} = -2.5 \text{ V},  I_D = -9 \text{ A}$ $V_{GS} = -4.5 \text{ V}, I_D = -10 \text{ A}, T_J = 125 ^{\circ}\text{C}$		8.5 11 11	13 17 20	mΩ
I <sub>D(on)</sub>	On-State Drain Current	$V_{GS} = -4.5 \text{ V},  V_{DS} = -5 \text{ V}$	-50			Α
<b>G</b> FS	Forward Transconductance	$V_{DS} = -5 \text{ V}, \qquad I_{D} = -10 \text{ A}$		57		S
Dvnamic	Characteristics			ı		ı
C <sub>iss</sub>	Input Capacitance	$V_{DS} = -10 \text{ V},  V_{GS} = 0 \text{ V},$		4951		pF
Coss	Output Capacitance	f = 1.0 MHz		884		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			451		pF
Switchin	g Characteristics (Note 2)			ı		ı
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = -10V$ , $I_{D} = -1 A$ ,		16	29	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = -4.5 \text{ V},  R_{GEN} = 6 \Omega$		9	18	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			196	314	ns
t <sub>f</sub>	Turn-Off Fall Time			78	125	ns
Qg	Total Gate Charge	$V_{DS} = -10 \text{ V},  I_{D} = -10 \text{ A},$		53	74	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = -4.5 V		6		nC
Q <sub>gd</sub>	Gate-Drain Charge			12		nC
Drain-So	ource Diode Characteristics	and Maximum Ratings		•		
ls	Maximum Continuous Drain-Source				-2.1	Α
V <sub>SD</sub>	Drain–Source Diode Forward Voltage	$V_{GS} = 0 \text{ V},  I_S = -2.1 \text{ A}  \text{(Note 2)}$		-0.6	-1.2	V

<sup>1.</sup> R ALA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.

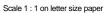


a) 50 °C/W when mounted on a 1in² pad of 2 oz copper





c) 125 °C/W when mounted on a minimum pad.



2. Pulse Test: Pulse Width  $< 300\mu s$ , Duty Cycle < 2.0%

# **Typical Characteristics**

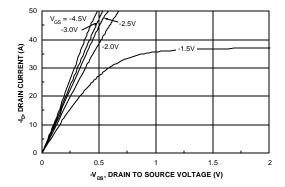


Figure 1. On-Region Characteristics.

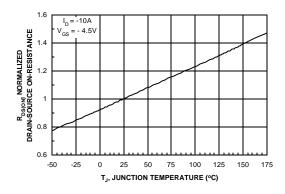


Figure 3. On-Resistance Variation with Temperature.

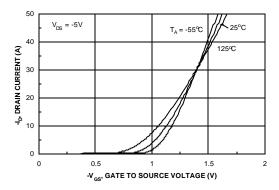


Figure 5. Transfer Characteristics.

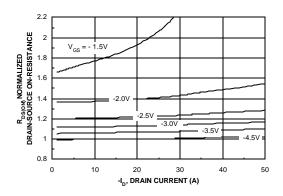


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

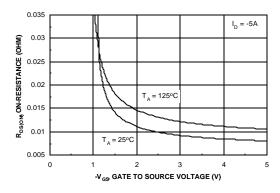


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

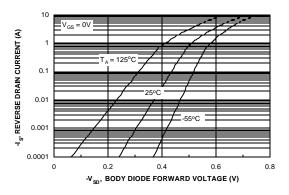
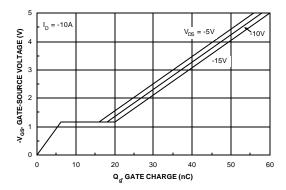


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

# **Typical Characteristics**



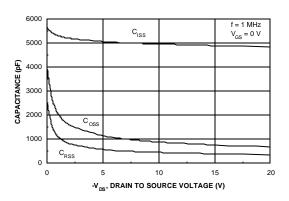
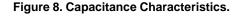
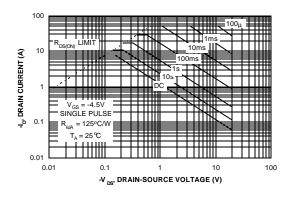


Figure 7. Gate Charge Characteristics.





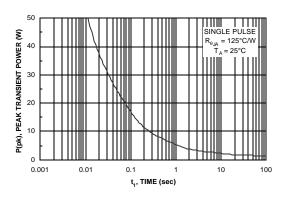


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

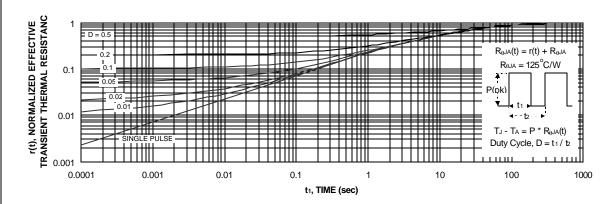


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

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